

Khalil Tamersit

List of Publications by Year in descending order

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times ranked

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citing authors

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 1 | Improved performance of sub-10-nm band-to-band tunneling n-i-n graphene nanoribbon field-effect transistors using underlap engineering: A quantum simulation study. <i>Journal of Physics and Chemistry of Solids</i> , 2022, 160, 110312. | 4.0 | 12 |
| 2 | Energy-Efficient Carbon Nanotube Field-Effect Phototransistors: Quantum Simulation, Device Physics, and Photosensitivity Analysis. <i>IEEE Sensors Journal</i> , 2022, 22, 288-296. | 4.7 | 8 |
| 3 | Synergy of Electrostatic and Chemical Doping to Improve the Performance of Junctionless Carbon Nanotube Tunneling Field-Effect Transistors: Ultrascaling, Energy-Efficiency, and High Switching Performance. <i>Nanomaterials</i> , 2022, 12, 462. | 4.1 | 11 |
| 4 | Role of Junctionless Mode in Improving the Photosensitivity of Sub-10 nm Carbon Nanotube/Nanoribbon Field-Effect Phototransistors: Quantum Simulation, Performance Assessment, and Comparison. <i>Nanomaterials</i> , 2022, 12, 1639. | 4.1 | 10 |
| 5 | Leveraging Negative Capacitance CNTFETs for Image Processing: An Ultra-Efficient Ternary Image Edge Detection Hardware. <i>IEEE Transactions on Circuits and Systems I: Regular Papers</i> , 2021, 68, 5108-5119. | 5.4 | 25 |
| 6 | Computational Investigation of Negative Capacitance Coaxially Gated Carbon Nanotube Field-Effect Transistors. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 376-384. | 3.0 | 27 |
| 7 | Improved Switching Performance of Nanoscale p-i-n Carbon Nanotube Tunneling Field-Effect Transistors Using Metal-Ferroelectric-Metal Gating Approach. <i>ECS Journal of Solid State Science and Technology</i> , 2021, 10, 031004. | 1.8 | 14 |
| 8 | A novel band-to-band tunneling junctionless carbon nanotube field-effect transistor with lightly doped pocket: Proposal, assessment, and quantum transport analysis. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2021, 128, 114609. | 2.7 | 23 |
| 9 | New nanoscale band-to-band tunneling junctionless GNFETs: potential high-performance devices for the ultrascaled regime. <i>Journal of Computational Electronics</i> , 2021, 20, 1147-1156. | 2.5 | 16 |
| 10 | Ultra-Compact Ternary Logic Gates Based on Negative Capacitance Carbon Nanotube FETs. <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , 2021, 68, 2162-2166. | 3.0 | 35 |
| 11 | Role of Underlap Structure in Boosting the Performance of Band-to-Band Tunneling Carbon Nanotube FET with 5-nm Gate Length. , 2021, , . | | 1 |
| 12 | Junctionless Carbon Nanotube Field-Effect Transistors as Gas Nanosensors for Low-Power Environment Monitoring Applications. , 2021, , . | | 0 |
| 13 | Analog/RF performance assessment of ferroelectric junctionless carbon nanotube FETs: A quantum simulation study. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2021, 134, 114915. | 2.7 | 17 |
| 14 | Improving the On-Current of Junctionless Carbon Nanotube Tunneling FETs Using a Heavily n-Type Doped Pocket. , 2021, , . | | 1 |
| 15 | Double-Gate Junctionless GNFETs Operating in the BTBT Regime: A Simple Design with Improved Performance for Low-Power Applications. , 2021, , . | | 0 |
| 16 | A new ultra-scaled graphene nanoribbon junctionless tunneling field-effect transistor: proposal, quantum simulation, and analysis. <i>Journal of Computational Electronics</i> , 2020, 19, 170-176. | 2.5 | 23 |
| 17 | Improving the performance of a junctionless carbon nanotube field-effect transistor using a split-gate. <i>AEU - International Journal of Electronics and Communications</i> , 2020, 115, 153035. | 2.9 | 25 |
| 18 | Computational Study of p-n Carbon Nanotube Tunnel Field-Effect Transistor. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 704-710. | 3.0 | 28 |

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 19 | Improved performance of nanoscale junctionless carbon nanotube tunneling FETs using dual-material source gate design: A quantum simulation study. AEU - International Journal of Electronics and Communications, 2020, 127, 153491. | 2.9 | 21 |
| 20 | Sub-10Ånm junctionless carbon nanotube field-effect transistors with improved performance. AEU - International Journal of Electronics and Communications, 2020, 124, 153354. | 2.9 | 33 |
| 21 | Profound analysis on sensing performance of Nanogap SiGe source DM-TFET biosensor. Journal of Materials Science: Materials in Electronics, 2020, 31, 22699-22712. | 2.2 | 22 |
| 22 | Performance enhancement of an ultra-scaled double-gate graphene nanoribbon tunnel field-effect transistor using channel doping engineering: Quantum simulation study. AEU - International Journal of Electronics and Communications, 2020, 122, 153287. | 2.9 | 28 |
| 23 | A new pressure microsensor based on dual-gate graphene field-effect transistor with a vertically movable top-gate: Proposal, analysis, and optimization. AEU - International Journal of Electronics and Communications, 2020, 124, 153346. | 2.9 | 25 |
| 24 | Boosting the performance of an ultrascaled carbon nanotube junctionless tunnel field-effect transistor using an ungated region: NEGF simulation. Journal of Computational Electronics, 2019, 18, 1222-1228. | 2.5 | 24 |
| 25 | A computational study of short-channel effects in double-gate junctionless graphene nanoribbon field-effect transistors. Journal of Computational Electronics, 2019, 18, 1214-1221. | 2.5 | 30 |
| 26 | Carbon Nanotube Field-Effect Transistor With Vacuum Gate Dielectric for Label-Free Detection of DNA Molecules: A Computational Investigation. IEEE Sensors Journal, 2019, 19, 9263-9270. | 4.7 | 37 |
| 27 | Performance Assessment of a New Radiation Dosimeter Based on Carbon Nanotube Field-Effect Transistor: A Quantum Simulation Study. IEEE Sensors Journal, 2019, 19, 3314-3321. | 4.7 | 31 |
| 28 | Quantum simulation of a junctionless carbon nanotube field-effect transistor with binary metal alloy gate electrode. Superlattices and Microstructures, 2019, 128, 252-259. | 3.1 | 31 |
| 29 | An ultra-sensitive gas nanosensor based on asymmetric dual-gate graphene nanoribbon field-effect transistor: proposal and investigation. Journal of Computational Electronics, 2019, 18, 846-855. | 2.5 | 29 |
| 30 | A computationally efficient hybrid approach based on artificial neural networks and the wavelet transform for quantum simulations of graphene nanoribbon FETs. Journal of Computational Electronics, 2019, 18, 813-825. | 2.5 | 26 |
| 31 | Atomistic Simulation of a New Label-Free DNA Nanosensor Based on Ballistic Carbon Nanotube Field-Effect Transistor. , 2019, , . | | 2 |
| 32 | Fast and Accurate Simulation of Ultrascaled Carbon Nanotube Field-Effect Transistor Using ANN Sub-Modeling Technique. , 2019, , . | | 1 |
| 33 | Numerical Study of a New Junctionless Tunneling Field-Effect Transistor Based on Graphene Nanoribbon. , 2019, , . | | 2 |
| 34 | Boosting the performance of a nanoscale graphene nanoribbon field-effect transistor using graded gate engineering. Journal of Computational Electronics, 2018, 17, 1276-1284. | 2.5 | 25 |
| 35 | A novel graphene field-effect transistor for radiation sensing application with improved sensitivity: Proposal and analysis. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2018, 901, 32-39. | 1.6 | 28 |
| 36 | Modeling of a new graphene-based smart sensor for high performance pH monitoring applications. , 2016, , . | | 2 |

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|----|---|-----|-----------|
| 37 | Double-Gate Graphene Nanoribbon Field-Effect Transistor for DNA and Gas Sensing Applications: Simulation Study and Sensitivity Analysis. IEEE Sensors Journal, 2016, 16, 4180-4191. | 4.7 | 107 |
| 38 | NEW DIELECTRIC MODULATED GRAPHENE (DMG) FETBASED SENSOR FOR HIGH-PERFORMANCE BIOMOLECULE SENSING APPLICATIONS. , 2015, , . | | 0 |
| 39 | Dual-Top-Gated Graphene field-effect transistors to improve the subthreshold swing for digital applications. , 2013, , . | | 2 |